

## Steps for CMOS process:

- 1) Draw the metal (blue) VDD & Vss rails in parallel and create a demarcation line in b/w. Allowing enough space b/w them for other CKT elements.
- 2) n-devices are placed below the demarcation line and p-devices are placed above the demarcation line.
- 3) n & p devices are then connected using metal and contacts.
- 4) Finally the remaining interconnections are made & control signals and data i/p's are added.

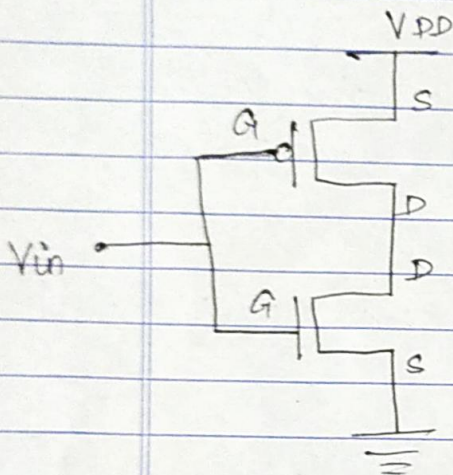
Note: \* diffusion paths must not cross the demarcation line

- \* n & p diffusion wires must not join.
- \* The metal should be used to connect n & p features
- \* we must place crosses (x) on VDD & Vss rails to represent the substrate and p-well connection respectively.
- \* only metal & polysilicon can cross the demarcation line
- \* Represent the Vss & VDD contact crosses -  
one on VDD line for every 4 p-transistors. &  
one on Vss line for every 4 n-transistors.

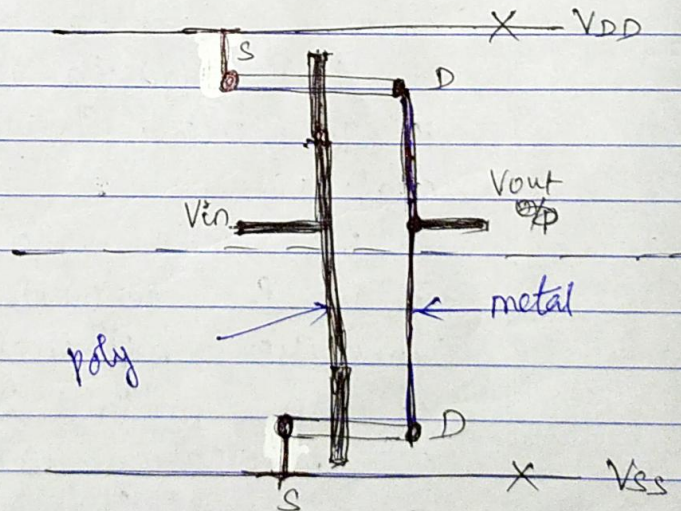
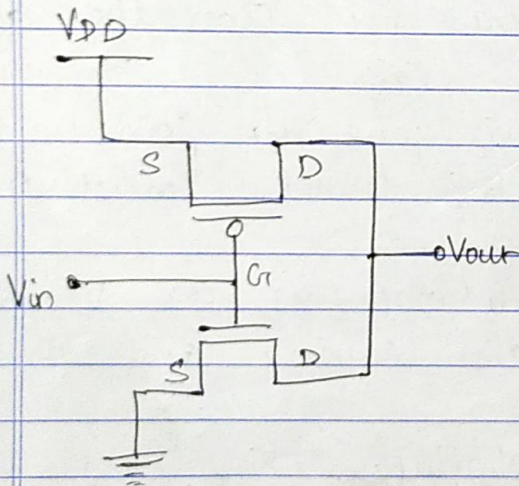
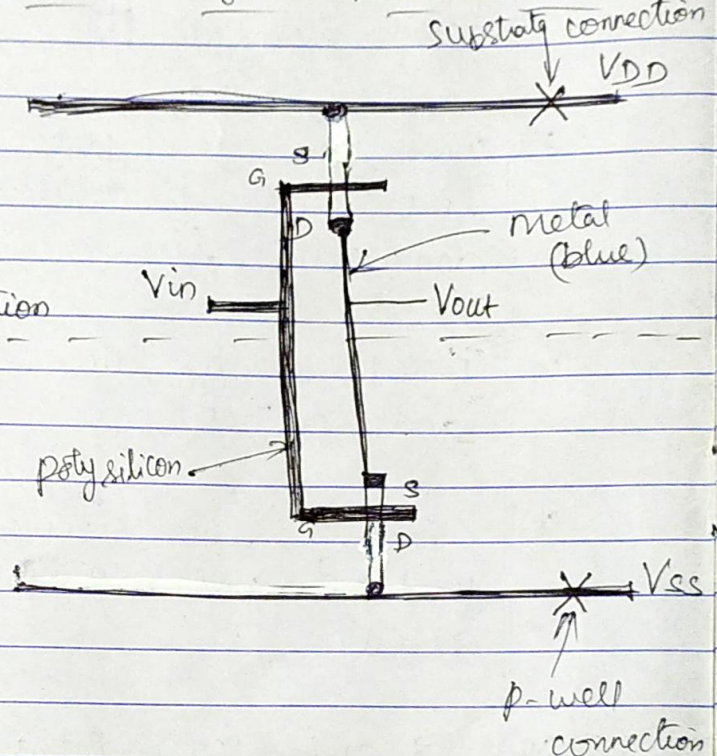


\* Metal lines on different layers (metal 1 & metal 2) can cross one another. Contacting 2 metal lines requires a via.

(1) write the ckt & stick diagram for CMOS inverter

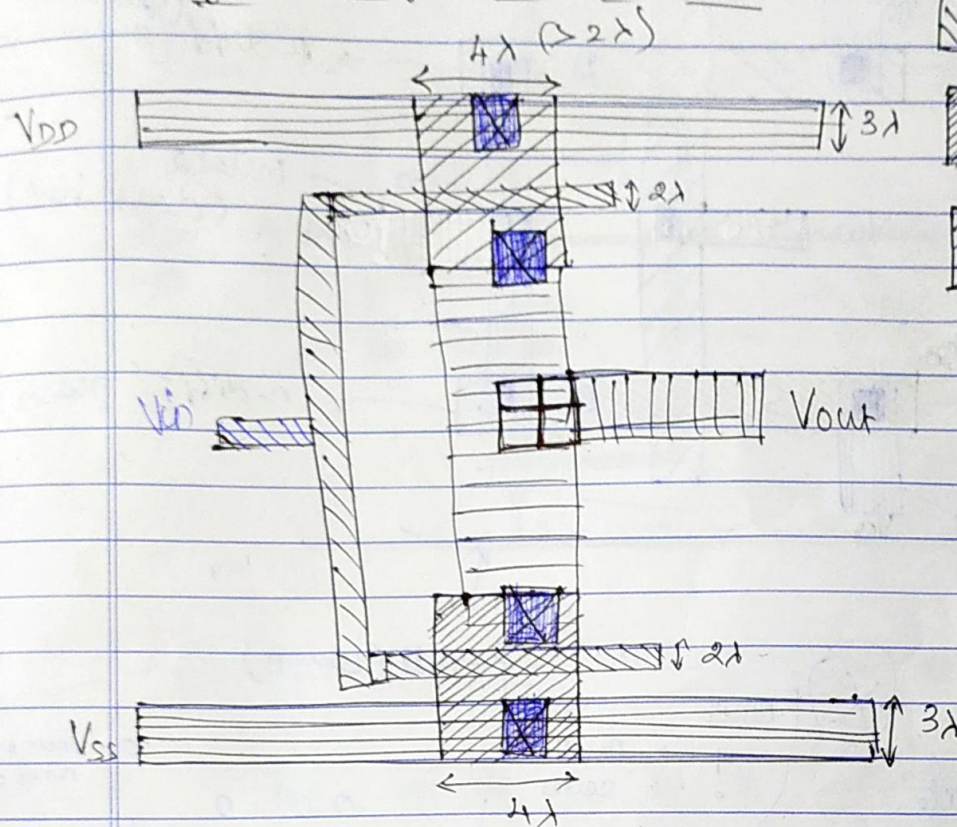


Ckt diagram.



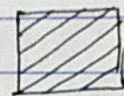

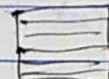


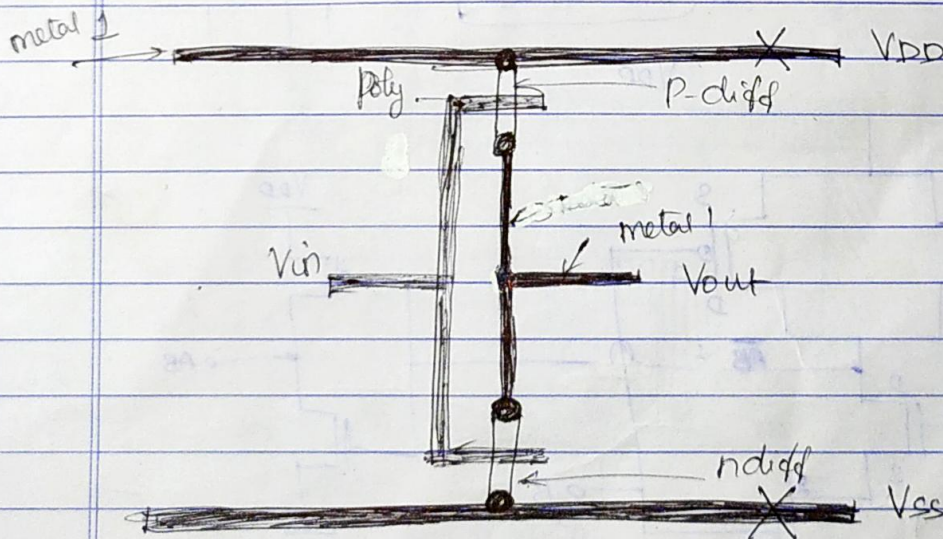


# Layout using $\lambda$ -based rules

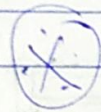
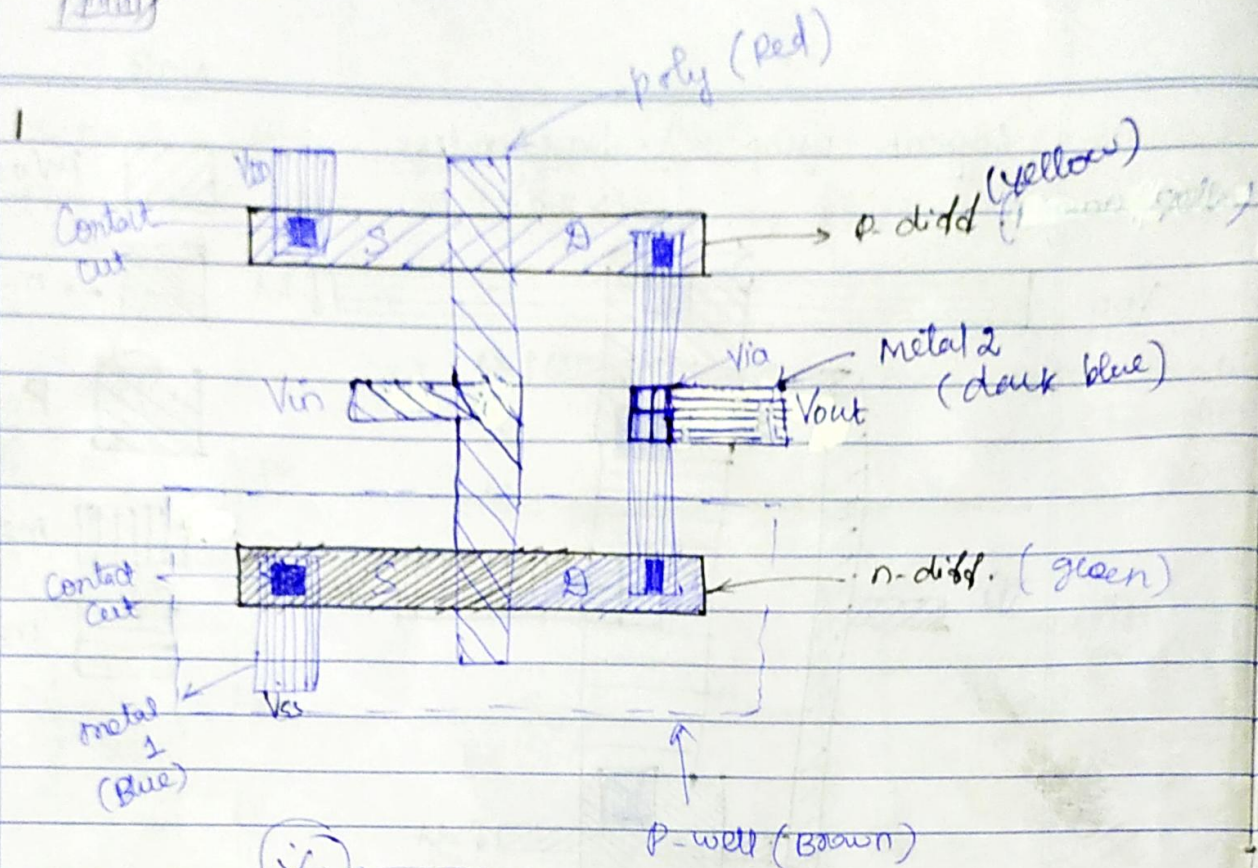


Note :-

-  polysilicon
-  n-diffusion
-  p-diffusion
-  metal-1
-  metal-2







NMOS

+ → Parallel  
• → series

PMOS

+ → series  
• → Parallel

0 → PMOS on  
NMOS off

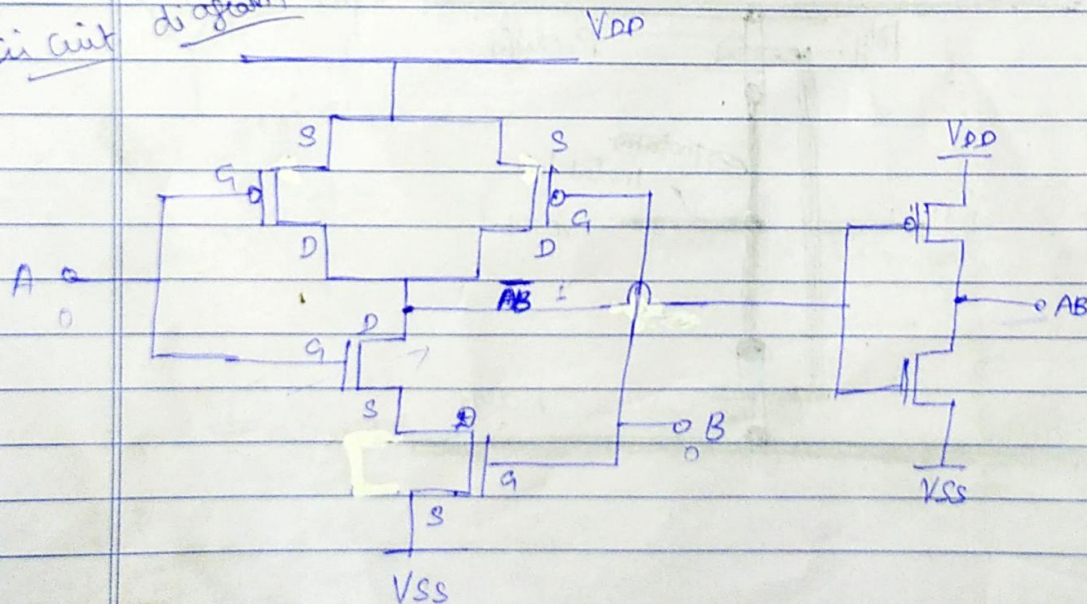
1 → NMOS on  
PMOS off

0	0	0
0	1	0
1	0	0
1	1	1

(ii) NAND gate:  
and AND

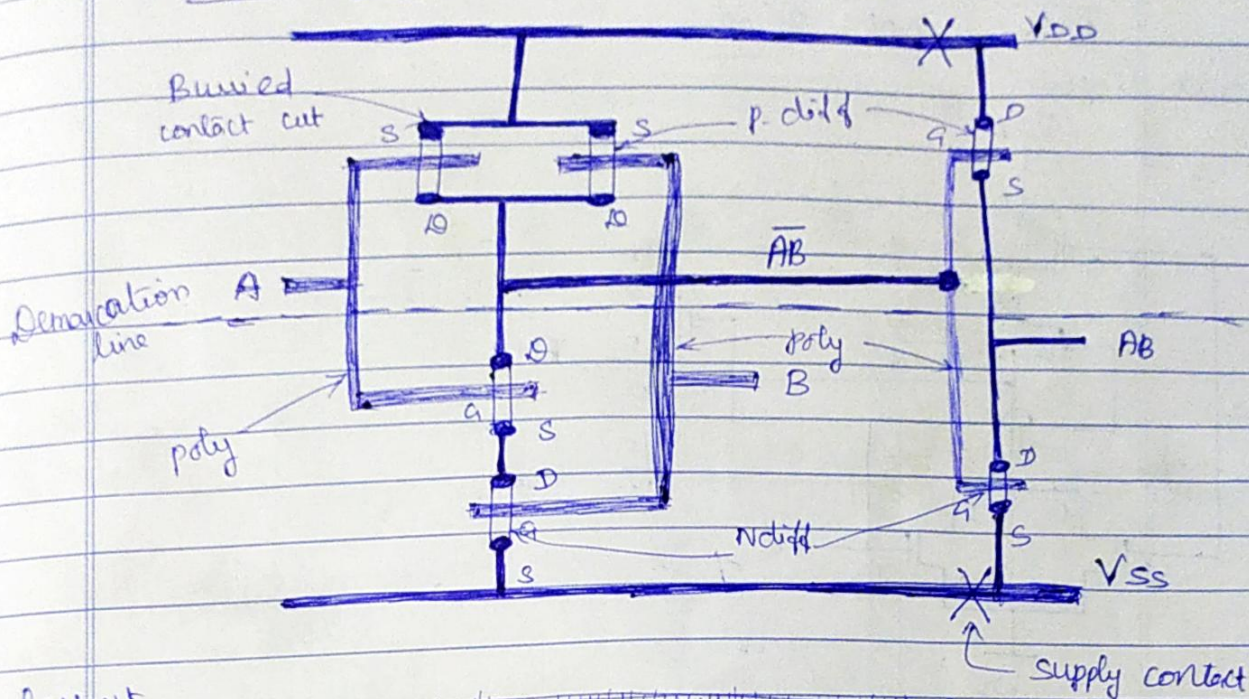
and gate  $Y = AB \Rightarrow Y = \overline{AB}$

circuit diagram

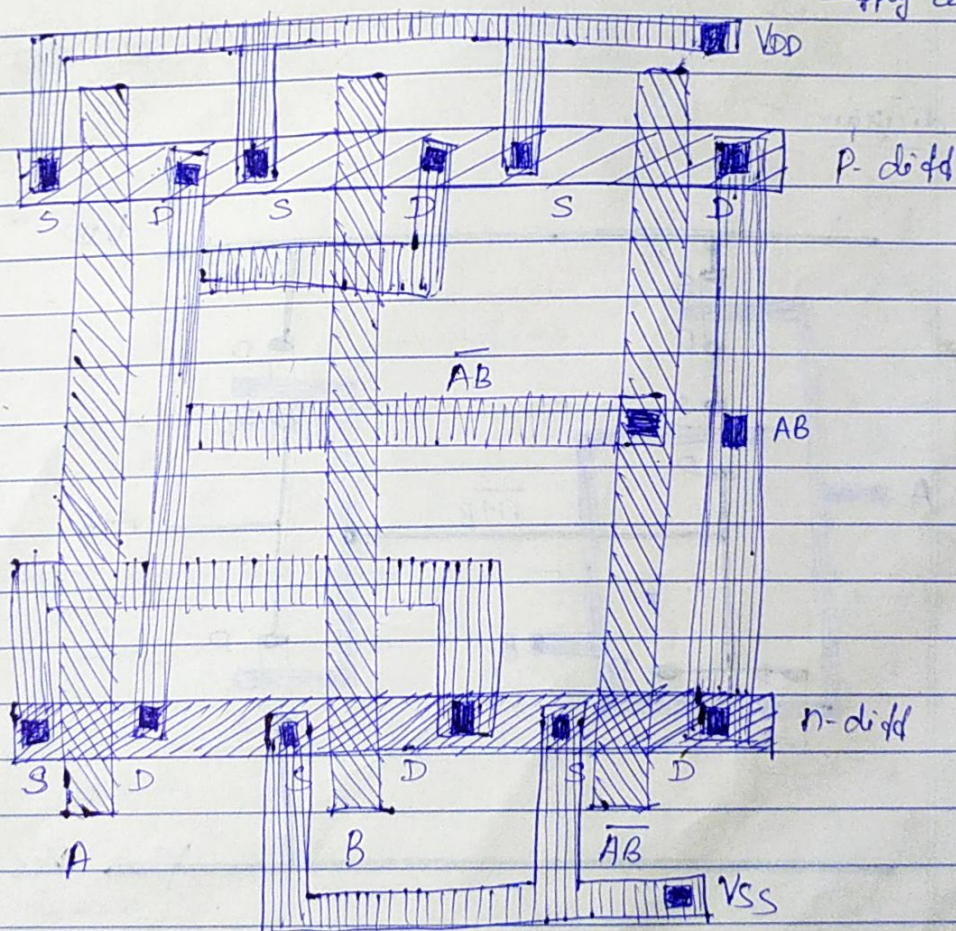




# Stick diagram



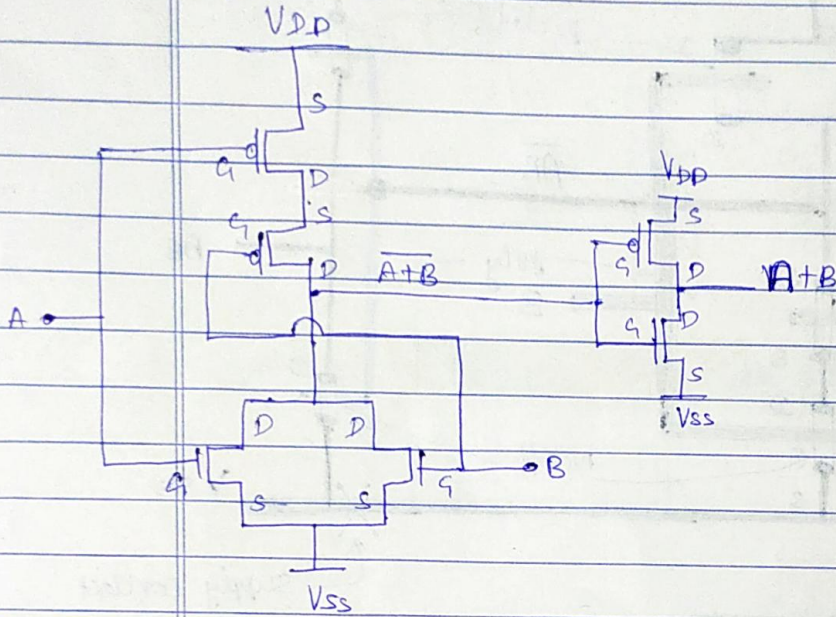
# layout



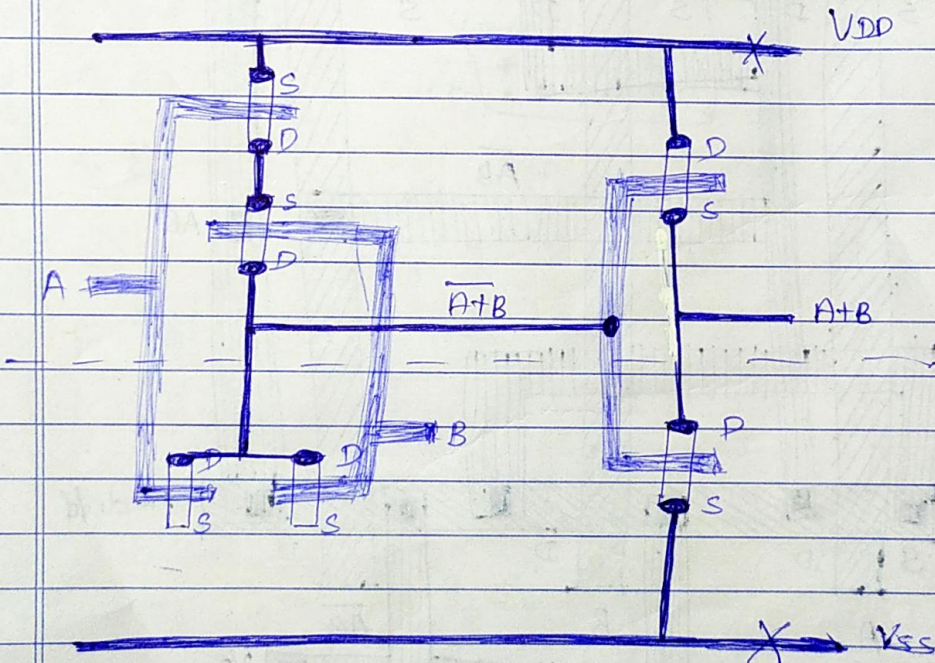


$$\overline{A+B} = \text{NOR} \ \& \ \text{OR}$$

circuit diagram

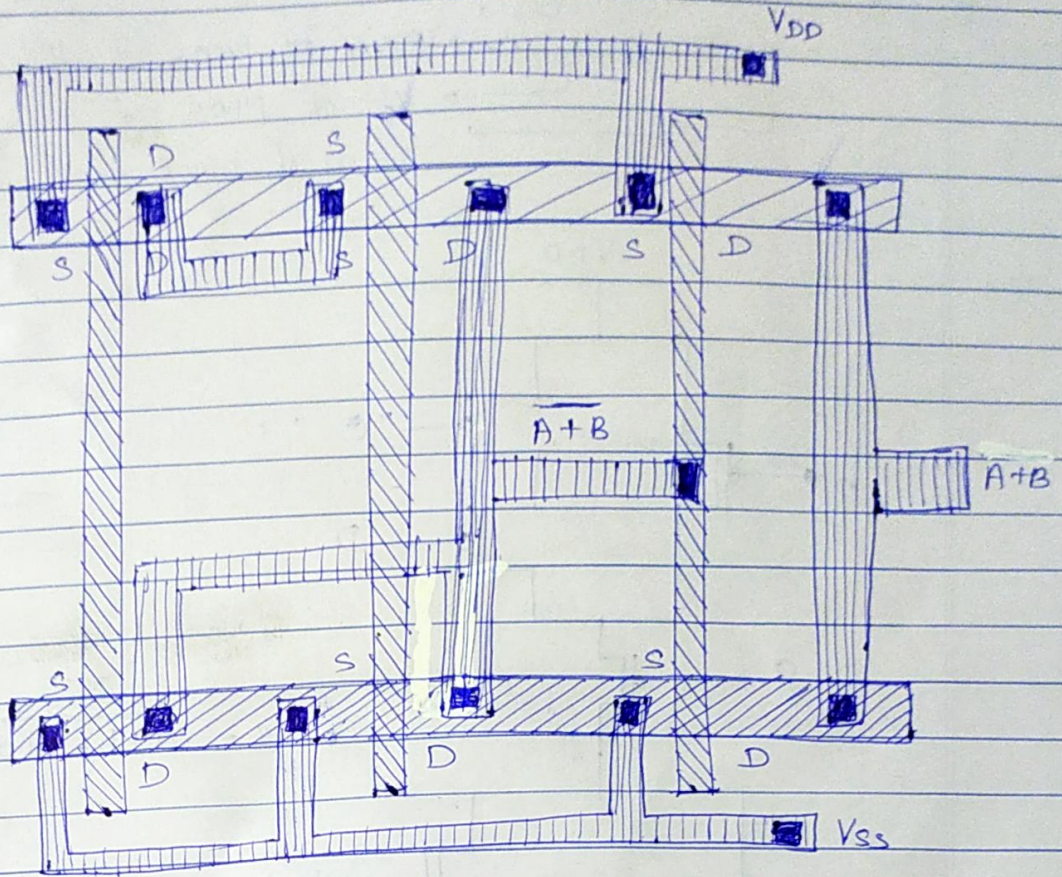


Stick diagram





layout

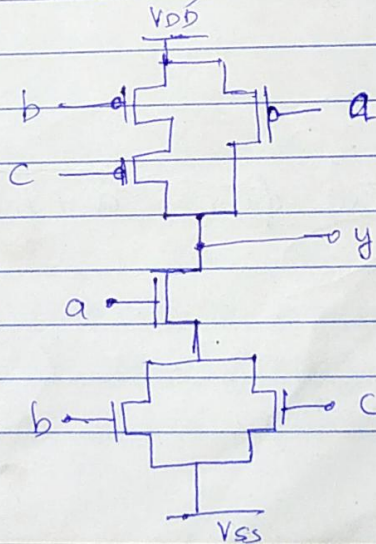


complex logic gates in CMOS:

+ 11el  
• series nmos

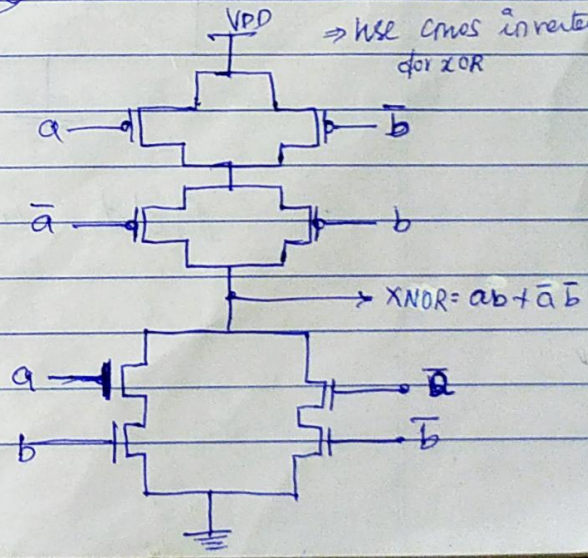
• 11el pmos  
+ series

①  $y = \overline{a \cdot (b+c)}$



②  $XOR = a \oplus b = \overline{a}b + a\overline{b}$

⇒ use CMOS inverters for XOR



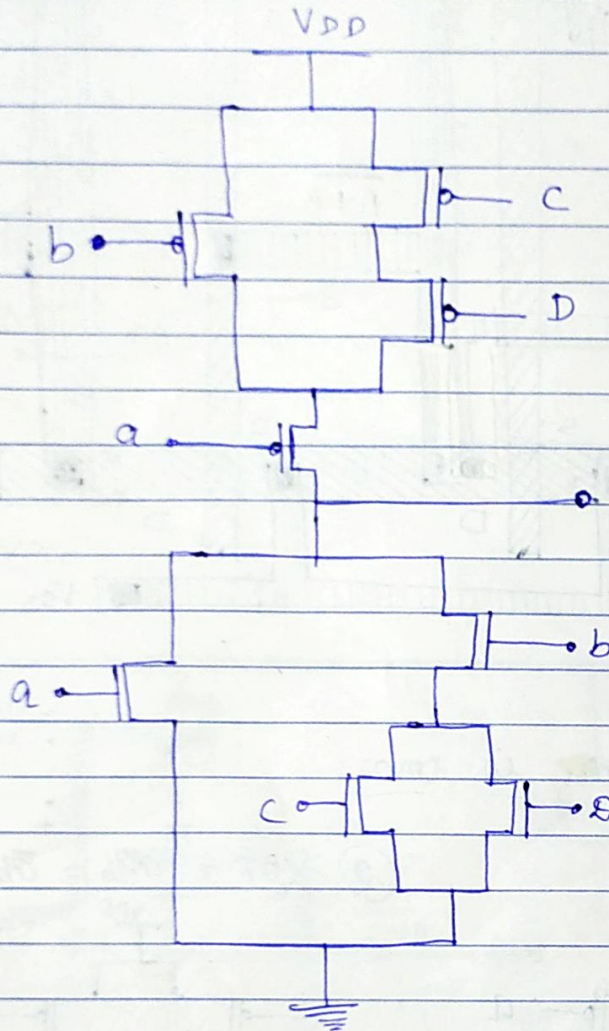


$$L = 2\lambda$$

$$\lambda = \frac{L}{2}$$

②  $X = \overline{a+b} \cdot (c+d)$

$\xrightarrow{\text{series of pmos + || of nmos}}$   
 $\xrightarrow{\text{|| of pmos + series of nmos}}$   
 $\xrightarrow{\text{series of pmos + || of pmos}}$



$\bullet X = \overline{a+b}(c+d)$

Add inverter for  $a+b(c+d)$